

**Vishay Semiconductors** 

## **Silicon PIN Photodiode**



#### DESCRIPTION

VBP104FAS and VBP104FASR are high speed and high sensitive PIN photodiodes. It is a surface mount device (SMD) including the chip with a 4.4 mm<sup>2</sup> sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength 870 nm or 950 nm.

### FEATURES

- Package type: surface mount
- Package form: GW, RGW
- Dimensions (L x W x H in mm): 6.4 x 3.9 x 1.2
- Radiant sensitive area (in mm<sup>2</sup>): 4.4
- High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm emitters
- Fast response times
- Angle of half sensitivity:  $\phi = \pm 65^{\circ}$
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### **APPLICATIONS**

- · High speed detector for infrared radiation
- Infrared remote control and free air data transmissionsystems, e.g. in combination with TSFFxxxx series IR emitters

PRODUCT SUMMARY				
COMPONENT	I <sub>ra</sub> (μA)	φ <b>(deg)</b>	λ <sub>0.5</sub> (nm)	
VBP104FAS	35	± 65	780 to 1050	
VBP104FASR	35	± 65	780 to 1050	

#### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
VBP104FAS	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing	
VBP104FASR	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing	

#### Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V <sub>R</sub>	60	V
Power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	Pv	215	mW
Junction temperature		Tj	100	°C
Operating temperature range		T <sub>amb</sub>	- 40 to + 100	°C
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C
Soldering temperature	Acc. reflow sloder profile fig. 8	T <sub>sd</sub>	260	°C
Thermal resistance junction/ambient		R <sub>thJA</sub>	350	K/W

#### Note

 $T_{amb}$  = 25 °C, unless otherwise specified





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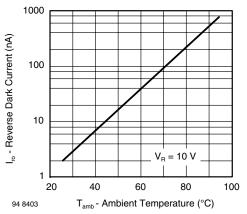
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 50 mA	V <sub>F</sub>		1	1.3	V
Breakdown voltage	I <sub>R</sub> = 100 μA, E = 0	V <sub>(BR)</sub>	60			V
Reverse dark current	V <sub>R</sub> = 10 V, E = 0	I <sub>ro</sub>		2	30	nA
Diode capacitance	$V_{R} = 0 V, f = 1 MHz, E = 0$	CD		48		pF
	V <sub>R</sub> = 3 V, f = 1 MHz, E = 0	CD		17	40	pF
Open circuit voltage	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of Vo	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	TK <sub>Vo</sub>		- 2.6		mV/K
Short circuit current	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	l <sub>k</sub>		32		μΑ
Temperature coefficient of $I_k$	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	ΤK <sub>Ik</sub>		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, \\ V_R = 5 \text{ V}$	I <sub>ra</sub>	25	35		μA
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λρ		950		nm
Range of spectral bandwidth		λ <sub>0.5</sub>		780 to 1050		nm
Noise equivalent power	$V_{R} = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4 x 10 <sup>-14</sup>		W/√Hz
Rise time	$V_{R} = 10 \text{ V},  \text{R}_{L} = 1  \text{k}\Omega, \\ \lambda = 820 \text{ nm}$	tr		100		ns
Fall time	$V_{R} = 10 \text{ V},  \text{R}_{L} = 1  \text{k}\Omega,$ $\lambda = 820 \text{ nm}$	t <sub>f</sub>		100		ns

#### Note

 $T_{amb} = 25 \ ^{\circ}C$ , unless otherwise specified

#### **BASIC CHARACTERISTICS**

 $T_{amb}$  = 25 °C, unless otherwise specified





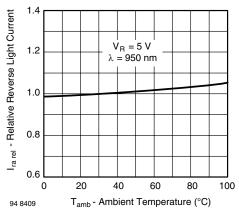


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



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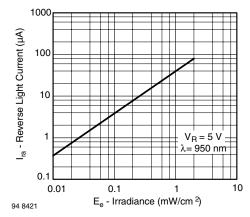


Fig. 3 - Reverse Light Current vs. Irradiance

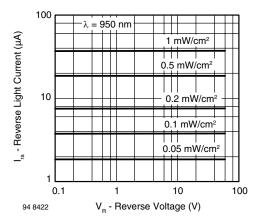


Fig. 4 - Reverse Light Current vs. Reverse Voltage

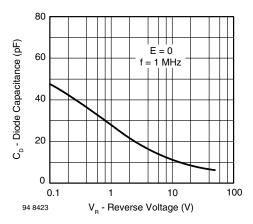


Fig. 5 - Diode Capacitance vs. Reverse Voltage

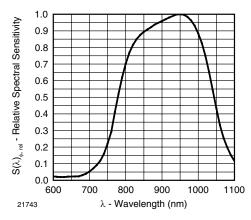


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

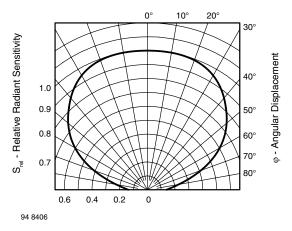


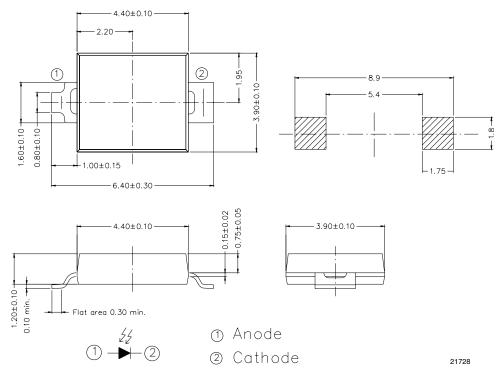
Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

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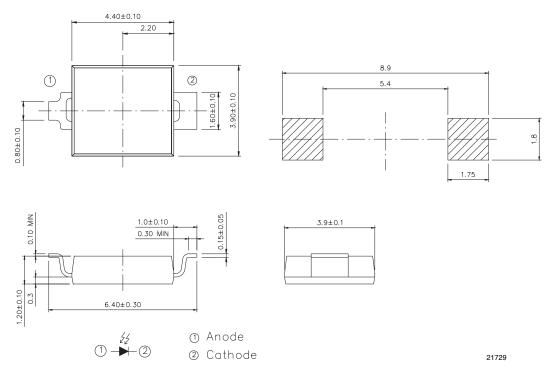
Silicon PIN Photodiode



### PACKAGE DIMENSIONS FOR VBP104FAS in millimeters



#### PACKAGE DIMENSIONS FOR VBP104FASR in millimeters

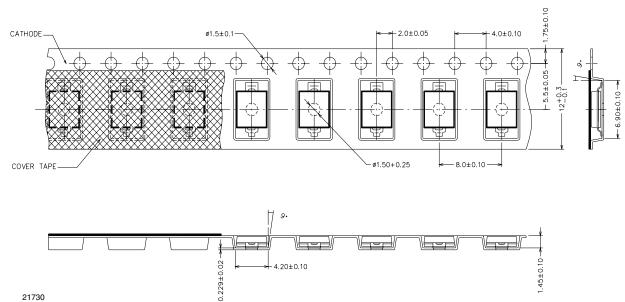




### Silicon PIN Photodiode

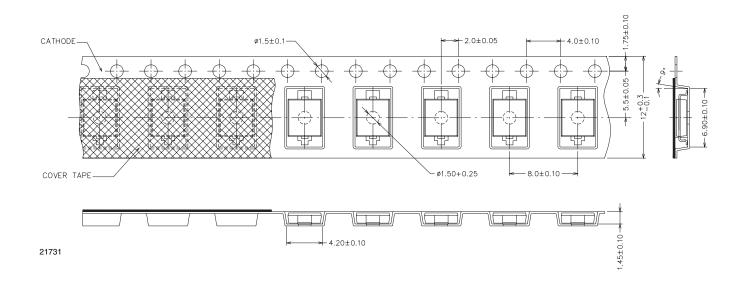
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### TAPING DIMENSIONS FOR VBP104FAS in millimeters



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#### TAPING DIMENSIONS FOR VBP104FASR in millimeters

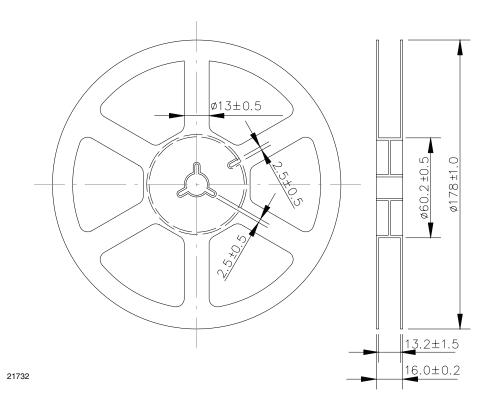


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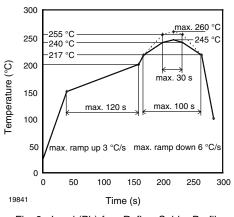
Silicon PIN Photodiode

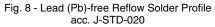


### REEL DIMENSIONS FOR VBP104FAS AND VBP104FASR in millimeters



SOLDER PROFILE





#### DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

#### **FLOOR LIFE**

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020: Moisture sensitivity: level 3 Floor life: 168 h Conditions:  $T_{amb} < 30$  °C, RH < 60 %

#### DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions: 192 h at 40 °C (+ 5 °C), RH < 5 % or 96 h at 60 °C (+ 5 °C), RH < 5 %.



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